THE RECORD OF LEARNING AND FORGETTING THE PROCESS OF MAGNETIZATION

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The development of spontaneous magnetization in a weak ferromagnet (Mn formate $2H_2O$) was studied in detail around T_N (3.686K) under very weak external magnetic field H_N lower than 10mOe by the use of SQUID magnetometer. The rather complicated but reproducible signals were found in the course of sweeping the temperature down and up through T_N. It was revealed that the memory of magnetization process was learnt in ordered region below T_N and kept even for two hours in some higher temperatures ($\mathcal{E}^{\leq}1\times10^{-2}$) than T_N. The memory was lost when the sample warmed up to $=5\times10^{N_2}2$.

1. Introduction - Development of spontaneous magnetization

We studied in detail the development of spontaneous magnetization M under very weak external field H by the use of SQUID magnetometer. The crystal we investigated, is Mn formate 2H₂O which is an antiferromagnet with very weak canting ferromagnetic moment.

When the external field was reduced to lower than 10m0e, Ishizuka detected the development of M with irregular fluctuation just around T at 3.686K, as shown in Fig. 1, in the course of sweep from higher to lower temperature across T. The phenomena might be attributed to the development of ferromagnetic clusters under nearly zero external field. We guess the analogy of the phenomena with the development of the droplets in zero gravitational space.

We studied the phenomena with very precise control of temperature and external field, and tried to detect any reproducibility in the course of cooling down and warming up, even though how irregular it is.



Fig. 1

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2. Learning and Forgetting, how?

In the following figures, we give M (arbitrary unit) as a function of $\mathcal{E} = (T-T_N)/T_N$, left hand side is in paramagnetic region, the dotted lines at about center indicates the position of T_N and right hand side is in ordered region. We start the sweeping of temperature from \mathcal{E} , and stop the cooling at about $\mathcal{E} = -2 \times 10^{-2}$. H gives the very weak external field value (not giving absolute but relative value, for instance in the case of Fig. 3, absolute zero field is somewhere between 4.56 and 3.99mQe.)

Now, in Fig. 2, we start from $\mathcal{E} = 1.1 \times 10^{-2}$ in every run of $(1) \sim 0$. M repeated almost the same to each other under the same H = 6.04m0e. They^Slearn the features of M. To forget them, warming up to $\mathcal{E} \ge 5.3 \times 10^{-2}$, is necessary and perhaps sufficient as seen from 8.

Fig, 3 shows the effect of changing H on changing the memory once obtained. No substantial change was not observed between (1) and (2) when \mathcal{E}_s was $\cong 1.1 \times 10^{-2}$ in each run. However, the drastic change of the memory was observed between (2) and (3) when \mathcal{E}_s was changed to 5×10^{-2} after (2). As M developed towards just the other direction, absolute zero field would be just between 4.56 and 3.99mOe.





Fig. 2

Fig. 3

3. Learning and Forgetting, where?

From these studies, we could have a guess the crystal learnt the ways of the development of M and got the memory of them in the long range order region lower than T_N , and they did not forget it in some short range order region, if the temperature of the crystal did not rise up to so high, say $\mathcal{E}=5\times10^{-2}$.

Fig, 4 shows the very existence of the boundary of the region where the learning of M would start. The first run (1) shows that M goes upwards under H =6.84mOe. And the second run (2) suggests that if H shifts to 0.00mOe in paramagnetic region. M will go downwards. Even if the temperature of this shift approaches much closer to T in short range order region, as shown in (3)~G, M goes still downwards. Surprizing enough, M in (6) keeps going upwards

if the shift from 6.84 to 0.00mOe is given just after crossing $T_{\rm N}$ line.

This is a definite indication that the direction of the dev $\stackrel{>}{\sim}$ lopment of spontaneous magnetization and the building up of memory would be assumed just after the starting of long range order array below T_N .



Fig. 4

Fig. 5

4. The memory, its reproducibility

The last Fig. 5 shows the trace of M in the course of cooling down and warming up under the same H for each run. The memories or features of M are reproduced exactly, as a whole, in amplitude and also in its position of bending on temperature scale. Some details are not reproduced suggesting that there are a kind of hierarchy in themselves. The details of experimental methods and results will be published shortly elsewhere.